READ HEAD HAVING SPIN VALVE SENSOR WITH IMPROVED CAPPING LAYER

ABSTRACT

A capping layer (502) including thin films of ruthenium (Ru) (504) and a metallic oxide (506) are employed with a spin valve sensor (500) for maintaining the MR coefficient (dr/R) of the spin valve sensor (500) after being subjected to annealing steps which simulate hard backing of the photoresist layers in the insulation stack of a write head.

FIG 15